

80V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
80V	7.8 m Ω @ $V_{GS} = 10$ V	83A

Features

- 100% Unclamped Inductive Switching (UIS) Test in Production -Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Description and Applications

This new generation MOSFET is designed to minimize R_{DS(ON)}, yet maintain superior switching performance. This device is ideal for use in power management and load switch.

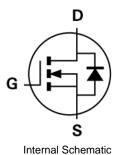
- DC-DC Converters
- Load Switch

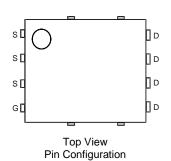
Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)









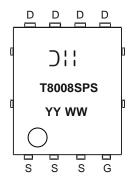
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT8008SPS-13	PowerDI5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



);; = Manufacturer's Marking T8008SPS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 19 = 2019)WW = Week (01 to 53)



Maximum Ratings (@T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	80	V
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current, V _{GS} = 10V (Note 7)	ID	83 66	А		
Maximum Continuous Body Diode Forward Current (Note 7)			I _S	69	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	330	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	330	Α
Avalanche Current, L = 0.1mH (Note 8)			I _{AS}	40	Α
Avalanche Energy, L = 0.1mH (Note 8)			Eas	80	mJ

Thermal Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P_{D}	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	95	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	44	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	P _D	83	W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	1.5	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@ $T_C = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	80	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 64V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	2	_	4	V	$V_{DS} = V_{GS}$, $I_D = 1mA$	
Static Drain-Source On-Resistance		_	6.5	7.8	mΩ	$V_{GS} = 10V, I_D = 14A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	_	7.8	11	11177	$V_{GS} = 6V, I_D = 12A$	
Diode Forward Voltage	V _{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_S = 14A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}		1950	_		$V_{DS} = 40V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	_	826	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	56	_			
Gate Resistance	Rg	_	1.7	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 6V)	Qg	_	23	_		V _{DS} = 40V, I _D = 14A	
Total Gate Charge (V _{GS} = 10V)	Qg	_	34	_	~C		
Gate-Source Charge	Qgs	_	6	_	nC		
Gate-Drain Charge	Q _{qd}	_	12	_			
Turn-On Delay Time	t _{D(ON)}		8	_		$V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 14A, R_{G} = 6\Omega$	
Turn-On Rise Time	t _R		15	_			
Turn-Off Delay Time	t _{D(OFF)}		29	_	ns		
Turn-Off Fall Time	t _F	_	21	_			
Body Diode Reverse Recovery Time	t _{RR}	_	43	_	ns	1 440 15/15 4000/11-	
Body Diode Reverse Recovery Charge	Q _{RR}	_	49	_	nC	I _S = 14A, di/dt = 100A/μs	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.





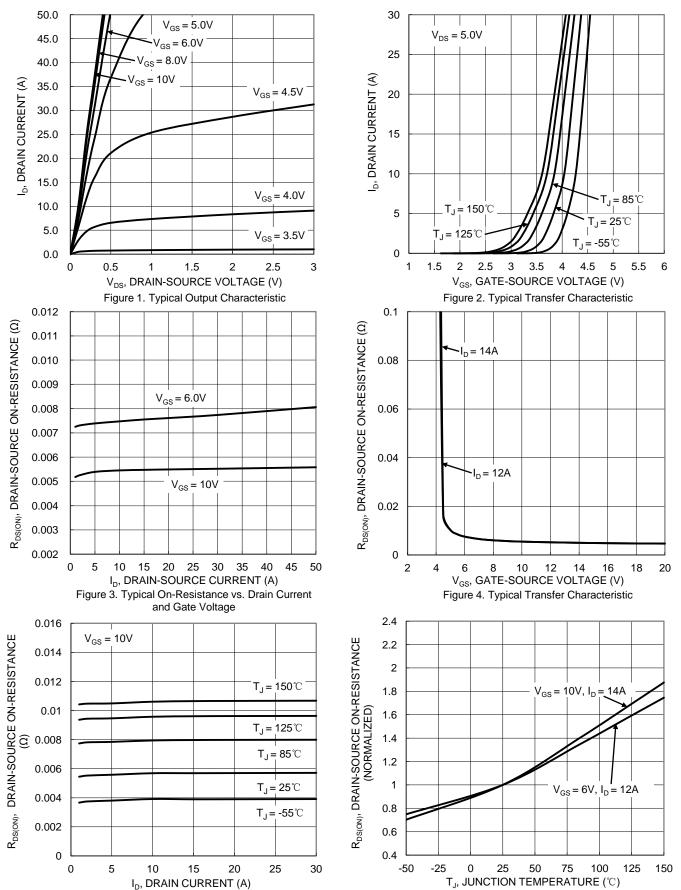


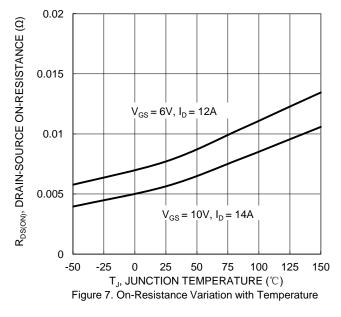
Figure 5. Typical On-Resistance vs. Drain Current

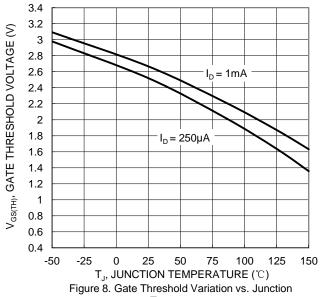
and Temperature

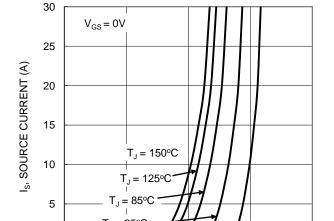
Figure 6. On-Resistance Variation with Temperature



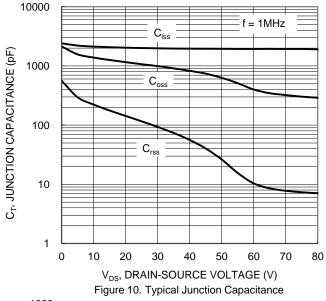








Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V)

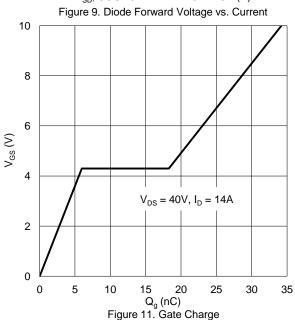
0.6

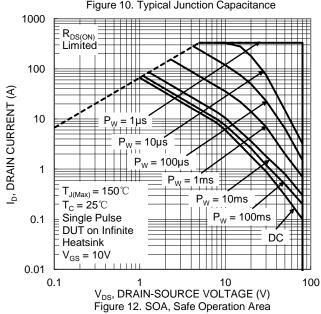
0.3

 $T_J = -55^{\circ}C$

1.2

0.9

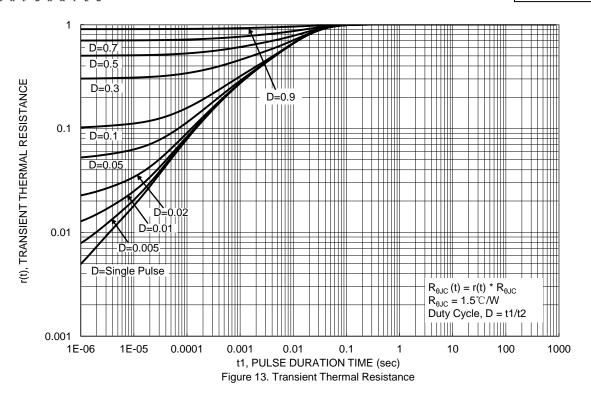




0

0



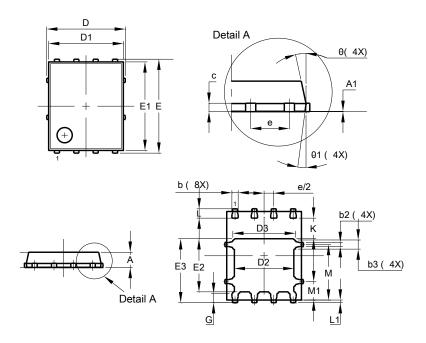




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

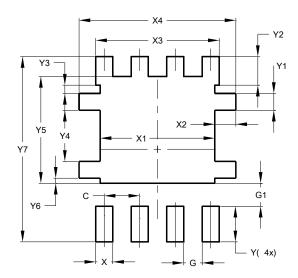


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A 1	0.00	0.05	_		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
C	0.230	0.330	0.277		
D		5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
E		6.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е		1.27 BSC			
G	0.51	0.71	0.61		
K	0.51	-	_		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Υ	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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